

# Reflection

- Specular or mirror like reflection from smooth surfaces
- Diffuse reflection from rough surfaces



## Specular X-ray Reflectivity

- A non-destructive, routine technique, used for estimation of density, thickness and roughness of thin film structures (single layer and multi-layered)
- Based on total external reflection of X-rays from surfaces and interfaces
- Can be used with amorphous, crystalline and liquid samples
- Used for typical layer thickness between 5 Å and 400 nm and surface roughness from 0 to 20 Å
- *This technique does not work effectively if there is no difference between the electron density of different layers or layer and substrate*



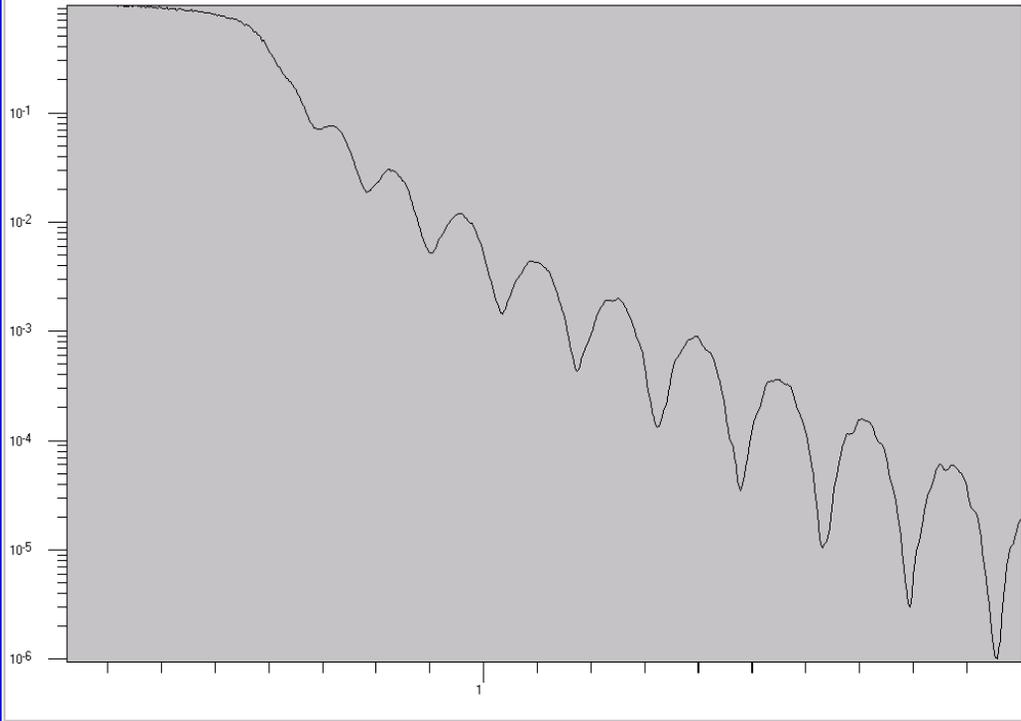
Incident Angle 1.6886 [deg]

Reflectivity:  $4.072 \times 10^{-4}$

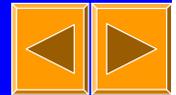
Max. measured Intensity: 848873664.0000

LOG

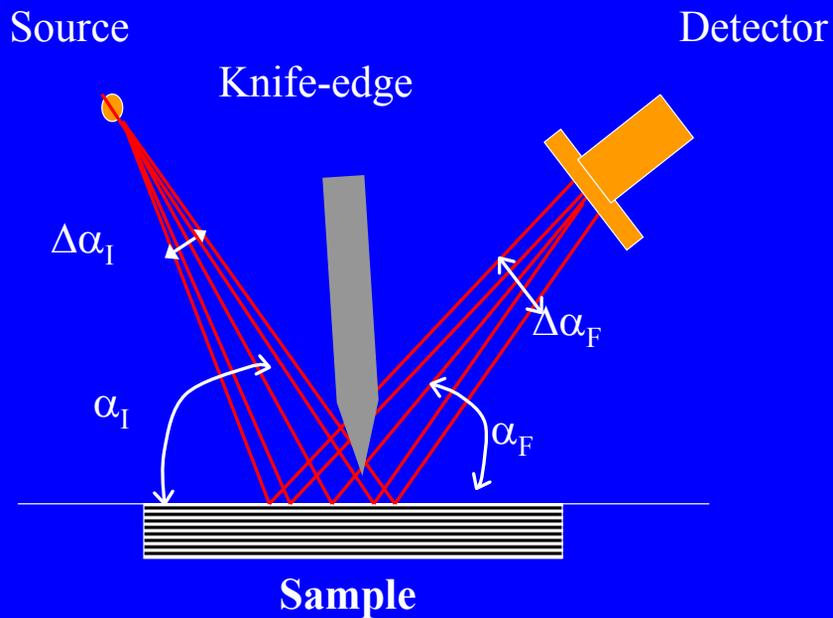
Normalized Reflectivity (Arbitrary Units)



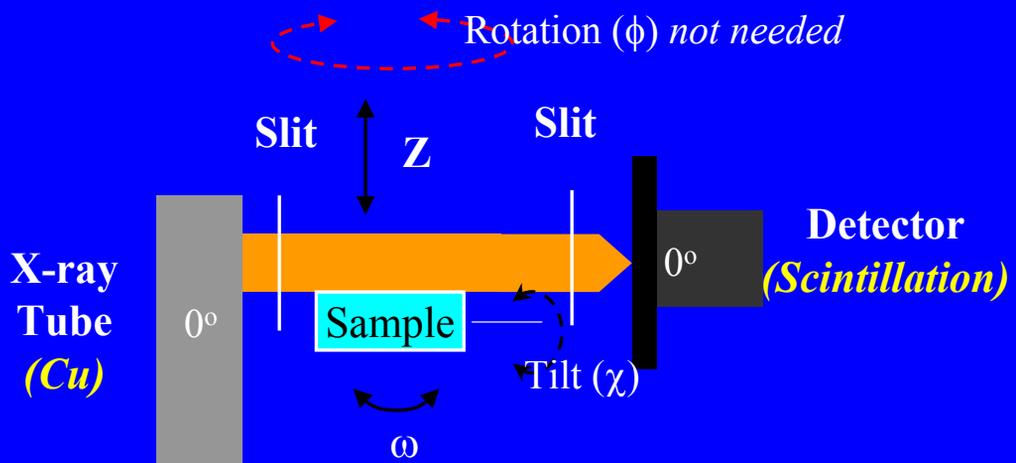
Incident Angle (degrees)



## Typical Measurement Setup



# Alignment



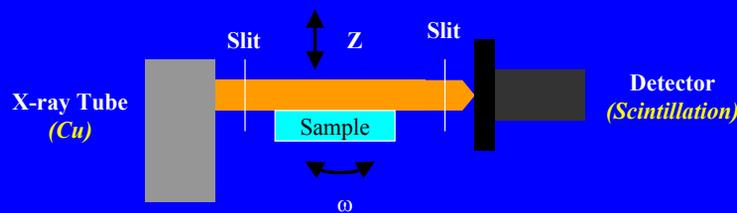
## Experimental Setup

- According to  $\alpha_1^{-4}$  law of Fresnel reflectivity, the intensity leaving a smooth surface decreases very rapidly on increasing the angle of incidence
- Since XRR requires recording reflected intensity over 5-6 orders of magnitude, highly intense X-ray source and detector with low noise are needed
- In order to measure the angles accurately, thus to minimize error in the results, the rotational axis of the sample circle ( $\omega$ -circle) has to be aligned exactly with the sample surface. This is accomplished in following steps:



## Sample Alignment

- Lateral movement and rocking sample across the primary beam ( $\omega$ -scan) are iterated until the maximum intensity of  $\omega$ -scans equals half the intensity of the primary beam, compared with the intensity measured without the sample. With this  $\omega$ -axis lies on the sample surface and this surface is parallel to the primary beam direction
- The angular position of the sample after the adjustment, however, may not coincide with the zero point of the  $\omega$ -circle. This is caused by various surface treatments or by the miscut of the sample surface with respect to any crystallographic main axis. The following step is required to redefine the  $\omega$ -scale.



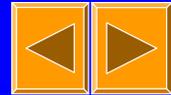
## Sample Alignment: Redefining $\omega$ -scale

- To redefine the  $\omega$ -scale we choose an angle of incidence ( $\alpha_1$ ) in the range  $0 < \alpha_1 < \alpha_c$ , where  $\alpha_c$  is the critical angle of incidence for total external reflection of X-rays. Typically this angle is chosen to be  $0.2^\circ$ .
- Angular position of the specularly reflected beam is measured on the detector circle  $2\theta$ . The sample surface is also corrected for any tilt ( $\chi$ -scan). If  $2\theta \neq 2\alpha_1$ ;  $\omega$  scale is readjusted by  $(2\theta/2 - \alpha_1)$ . This procedure may be repeated for different values of  $\alpha_1$  to improve the precision of the sample alignment

*This completes the sample alignment. This procedure is repeated for every sample.*

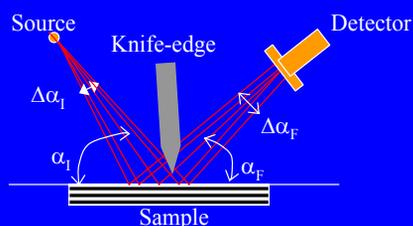
## Reflectivity Measurement: Setup

- Reflectivity experiments are optimized in such a way that the specular reflectivity and large features characterizing the sample (Bragg's peak, Kiessig oscillations) appear up to a large value of  $\alpha_1$  ( $\sim 2^\circ$ ).
- Higher angular resolution is needed to separate specular from diffuse scattering events. This can be achieved by decreasing angular divergence of incident beam ( $\Delta\alpha_1$ ) and angular acceptance of detector ( $\Delta\alpha_F$ ). In practice low  $\Delta\alpha_1$  and ( $\Delta\alpha_F$ ) can be obtained by using narrow slits at incident beam and detector side respectively. However, narrow slits decrease the intensity thus increasing the experimental time.
- To obtain high resolution and good scattered intensity, the following steps are taken



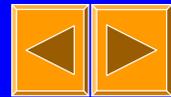
## Reflectivity Measurement: Setup

- As a trade-off, higher values  $\Delta\alpha_1$  and  $\Delta\alpha_F$  (hence wider slits) are used but the irradiated sample area is reduced to achieve sufficient angular resolution.
- In practice, this is achieved by using a knife-edge very close to the axis of sample rotation i.e. to the sample surface.
- Under these conditions only those beams leaving the sample surface directly below the knife-edge arrive at detector.

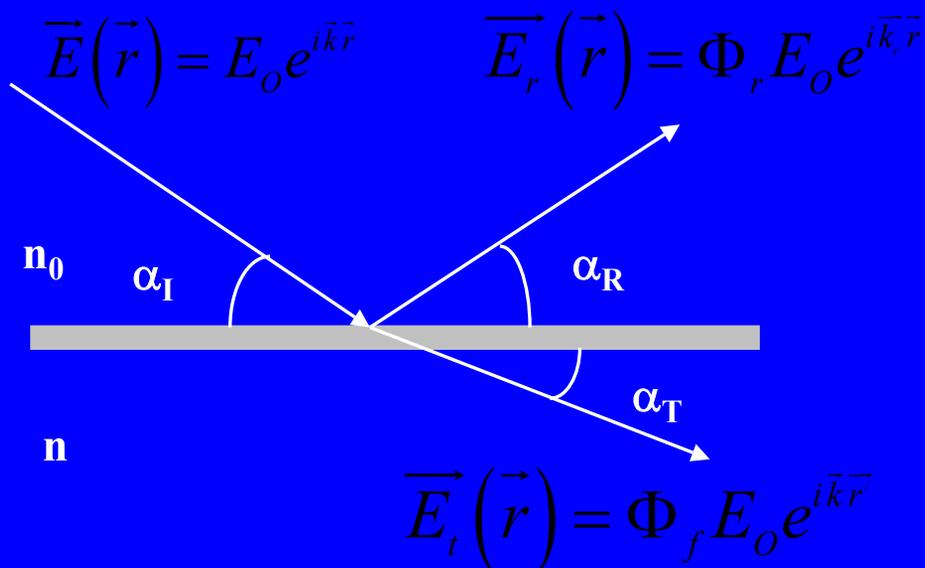


# Reflectivity Measurement

- Different ranges of the reflected curve are selected and recorded under various conditions of angular resolution and counting time. While the measurements near  $\alpha_C$  are carried out with highest resolution, angular resolution can be relaxed at higher angles. Typically measurements are setup to have at least 1500 counts for the maxima of each oscillation.
- The specular reflectivity is recorded while running  $\omega$ -2 $\theta$  scan, where  $\omega$  is the angular position of sample circle and 2 $\theta$  is the angular position of detector. In this scan,  $\alpha_I$  and angle of exit ( $\alpha_F$ ) are changed simultaneously and  $\alpha_I = \alpha_F$ .
- High resolution measurements with Four-bounce monochromator are typically for films thicker than  $\sim 0.5\mu\text{m}$



# Transmission and Reflection of X-rays



## Basic Equations: Density of Single layer

- At X-ray frequencies, the refractive index can be expressed as

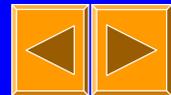
$$n = 1 - \delta - i\beta \quad (1)$$

Where

$$\delta = \left[ \frac{\rho_e r_e \lambda^2}{2\pi} \right] \quad \beta = \left( \frac{\mu \lambda}{4\pi} \right)$$

$\delta(\lambda)$  and  $\beta(\lambda) \sim 10^{-6}$  and describes the dispersion and absorption terms

- $\rho_e$  = electron density (Z electrons/ atom)
- $\lambda$  = wavelength of X-ray
- $\mu$  = linear absorption coefficient for energies far from X-ray threshold
- $r_e$  = classical electron radius =  $e^2/mc^2$



## Basic Equations: Density of Single layer

- For specular X-ray reflectivity  $\alpha_I = \alpha_R$ ; angle of incidence is equal to angle of exit.
- Since the real part of index of refraction of materials is less than unity (index of refraction for vacuum) the material is for X-rays less refractive than it is for vacuum.
- According for Snell-Descartes law

$$\frac{\cos \alpha_I}{\cos \alpha_T} = \frac{n}{n_0} \quad (2)$$



## Basic Equations: Density of Single layer

- There is a critical angle of incidence  $\alpha_C$  for which the X-rays are totally reflected at the interface, hence  $\alpha_T = 0$ . Neglecting the absorption in this case, we find

$$n \cong 1 - \delta = \frac{\cos \alpha_I}{\cos \alpha_T}$$

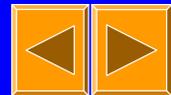
- Expanding the cosine for small angles

$$\alpha_c \approx \sqrt{2\delta} = 1.64 * 10^{-3} \sqrt{\rho_m} * \lambda \quad (3)$$

$$\rho_m = \frac{\rho_e A}{N_A Z}$$

where  $Z$  is the atomic number,  $A$  is the mass number and  $N_A$  is Avogadro's constant

$\alpha_C$  is determined at  $R(\alpha_p) = R_{max}/2$



## Basic Equation: Thickness of Single Layer

- Reflectivity of a single layer deposited on a semi-infinite substrate can be expressed as

$$R = \left| \frac{r_1 + r_2 e^{-2ik_{0z}t}}{1 + r_1 r_2 e^{-2ik_{0z}t}} \right|^2 \quad (4)$$

Where  $r_{1,2}$  are the Fresnel reflectivity coefficients of the free surface and the substrate interface respectively,  $k_{0z}$  is the vertical component of the wave vector of the beam transmitted through the layer and  $t$  is the layer thickness.

- Intensity maxima occurs whenever  $\exp(-2ik_{0z}t) = 1$   
i.e. at angle positions  $\alpha_{im}$



## Basic Equation: Thickness of Single layer

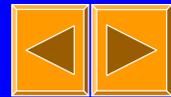
- Alternatively, for intensity maxima, the path difference between the reflected waves should be an integral multiple of the incident wavelength

$$2t\sqrt{\sin^2 \alpha_{Im} - \sin^2 \alpha_C} = m\lambda \quad (5)$$

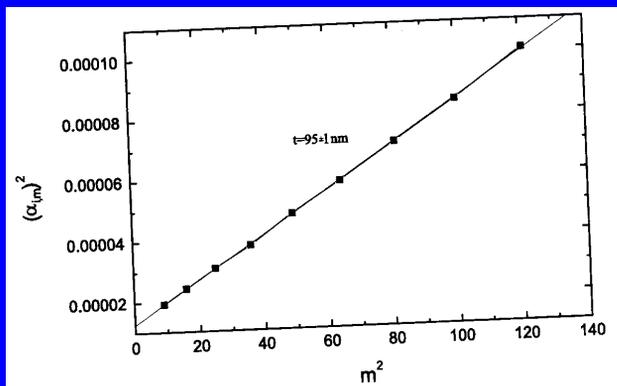
Where “m” is an integer

In most cases, the angle of incidence are small, hence (5) can be expressed as

$$\alpha_{Im}^2 - \alpha_C^2 = m^2 \left( \frac{\lambda}{2t} \right)^2 \quad (6)$$



## Thickness Calculation



- Squares of the positions of the intensity maxima versus squares of the Kiessig fringe order “m” is plotted
- The slope of the linear dependence is used to estimate layer thickness “t” while intercept of the line at  $m=0$  is used to determine  $\alpha_C$ .



## Accuracy in Estimation

- Accuracy in density is defined as

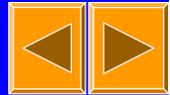
$$\frac{\Delta\rho}{\rho} = 2 \left( \frac{\delta\alpha_I}{\alpha_C} \right)$$

Where  $\delta\alpha_I$  is the step width of the goniometer

- Accuracy in thickness is defined as

$$\frac{\Delta t}{t} = \left( \frac{\delta\alpha_I}{\alpha_C} \right) \approx \frac{1}{m_{\max}}$$

Where  $m_{\max}$  is the largest fringe order that is detected in the reflectivity curve with an accuracy of one-half of a fringe period

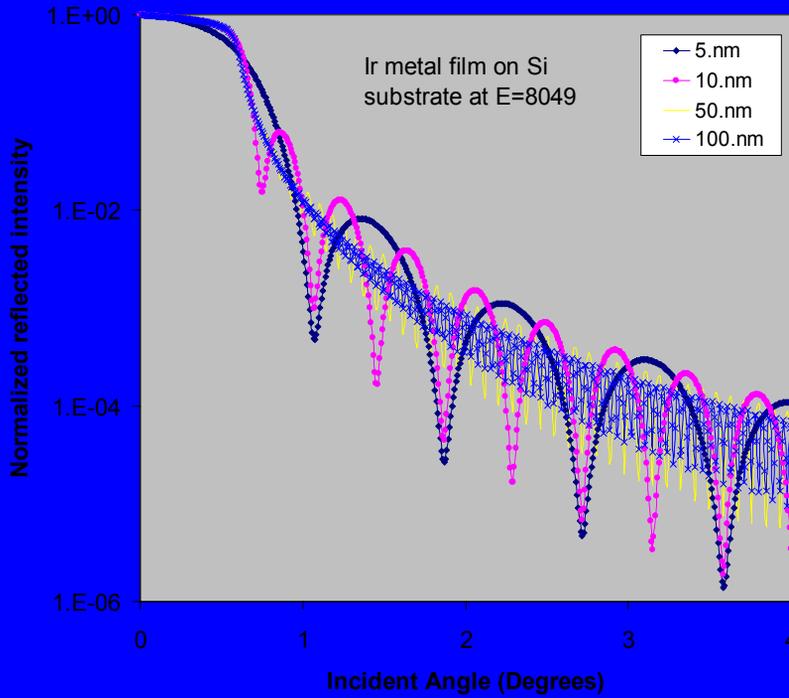


## Effect of Roughness

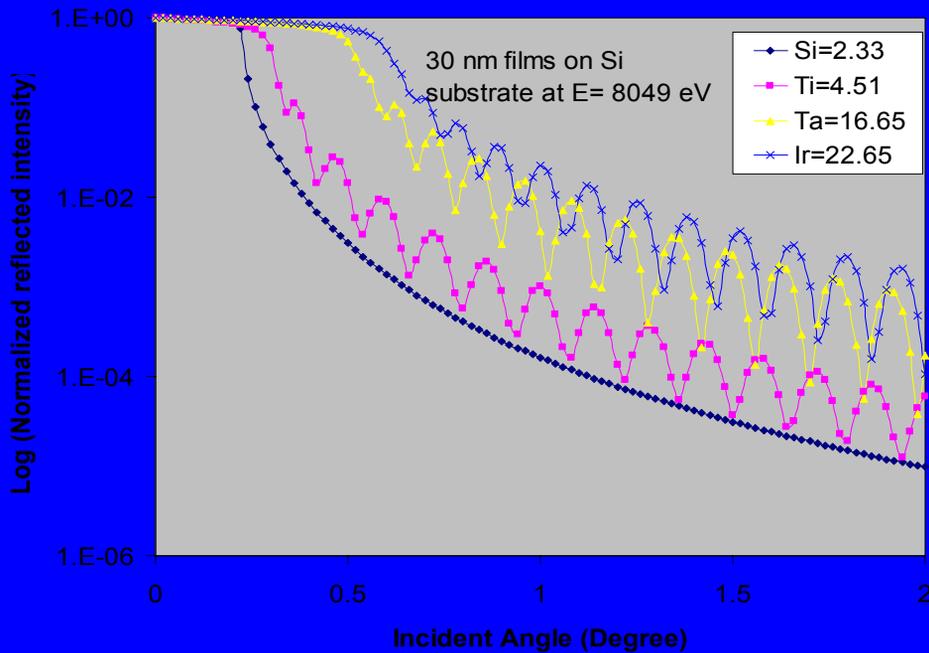
- In real world surfaces/ thin film structures are not perfectly smooth and possess surface and/or interface roughness
- While the presence of surface roughness decreases the specular intensity of the whole curve progressively, interface roughness gives rise to progressive damping of the Kiessig fringes.



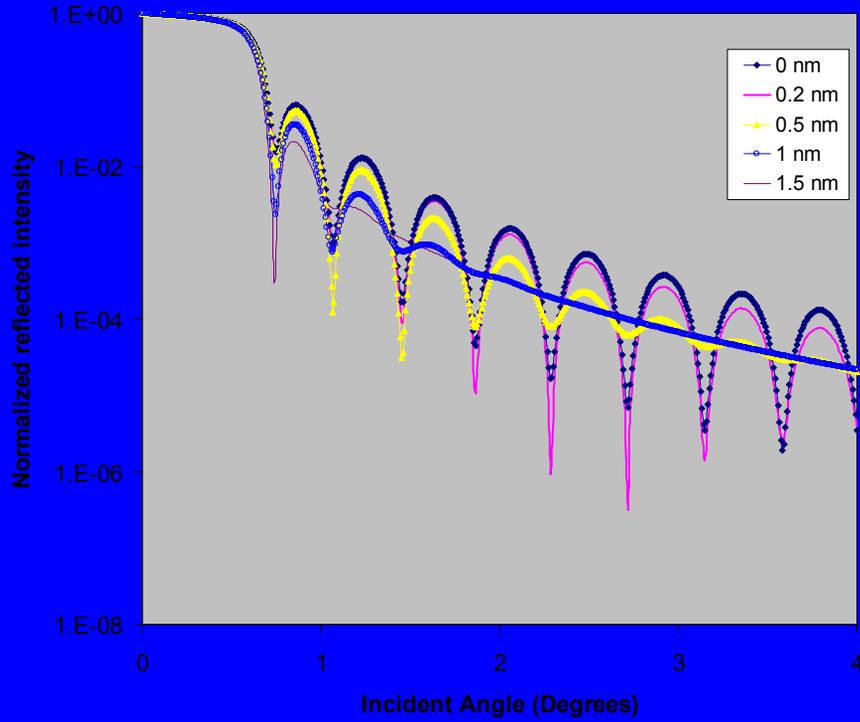
# Reflectivity curves for films with different thickness



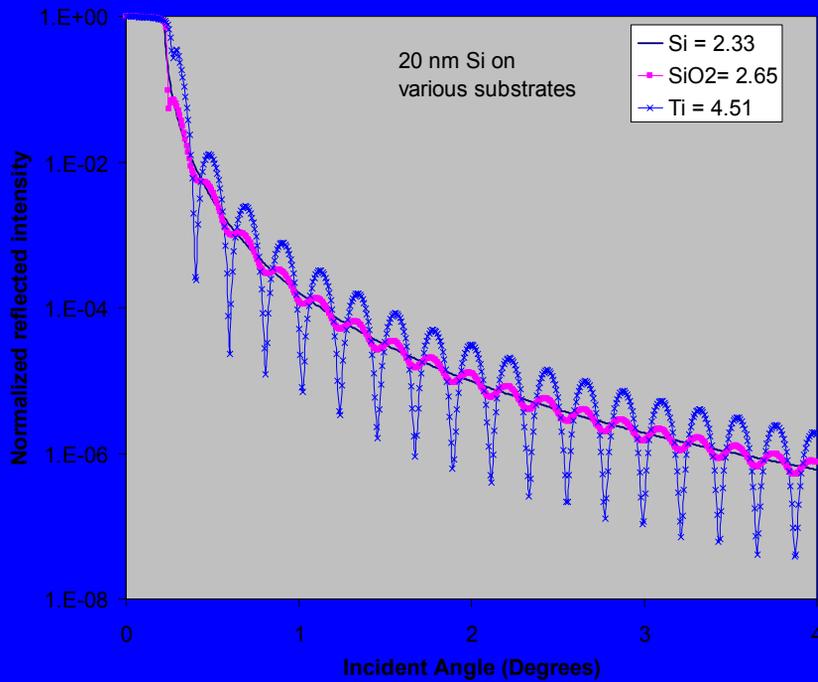
# Reflectivity curves for materials with different densities



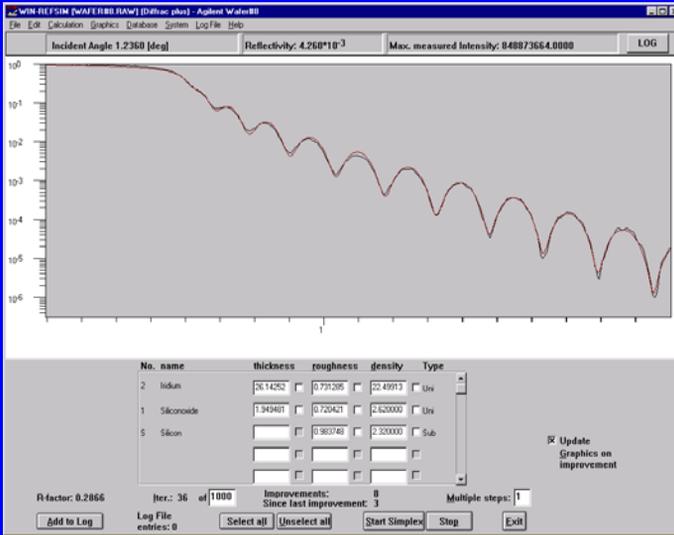
# Reflectivity curves for films with different film surface roughness



# Reflectivity curves for films with different substrate density

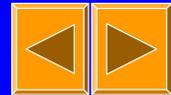


# Simulated Results: Ir metal on Si substrate



- Results are simulated starting with simplest structure; adding complexity as needed
- An attempt is made to have minimum difference between simulated and experimental results.

Red curve= simulated results;  
Grey curve = experimental results



## Suggested Readings

- REFSIM Version 1.2, User's Manual (Bruker AXS)
- High Resolution X-ray Scattering from Thin Films and Multilayers (V. Holy, U. Pietsch, T. Baumbach) Springer Tracts in Modern Physics



# Website of Interest

[http://cindy.lbl.gov/optical\\_constants](http://cindy.lbl.gov/optical_constants)

- X-ray specular reflectivity curves for single and multiple layers
- Estimation of depth penetration as a function of incident angle or energy

